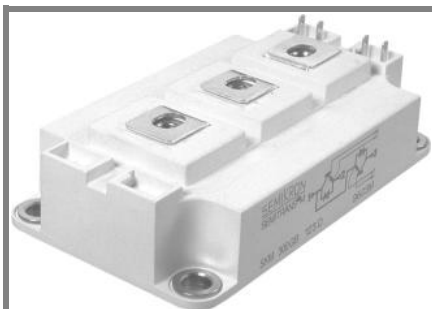




SEMITRANS® 3

Trench IGBT Modules

SKM 600GB066D

Features

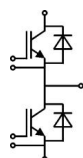
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_C$

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders

Remarks

- Case temp. limited. to $T = 125^\circ\text{C}$, recomm. $T_{op} = -40 \dots +150^\circ\text{C}$, product rel. results valid for $T_{j \leq 150^\circ\text{C}}$
- SC data: $t_p \leq 6\mu\text{s}$; $V_{GE} \leq 15\text{V}$; $T_j = 150^\circ\text{C}$; $V_{CC} \leq 360\text{V}$, use of soft R_G necessary !
- Take care of over-voltage caused by stray induct.
- $I_{DC} \leq 500\text{A}$ for $T_{Terminal} = 100^\circ\text{C}$

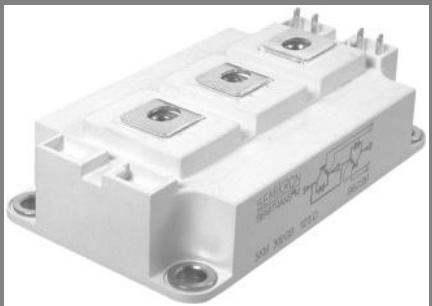


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Absolute Maximum Ratings				$T_{case} = 25^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions			Values	Units
IGBT					
V_{CES}	$T_j = 25^\circ\text{C}$			600	V
I_C	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$		760	A
		$T_c = 80^\circ\text{C}$		570	A
I_{CRM}	$I_{CRM} = 1,33 \times I_{Cnom}$			800	A
V_{GES}				± 20	V
t_{psc}	$V_{CC} = 360\text{V}$; $V_{GE} \leq 15\text{V}$; $T_j = 150^\circ\text{C}$ $V_{CES} < 600\text{V}$			6	μs
Inverse Diode					
I_F	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$		700	A
		$T_c = 80^\circ\text{C}$		510	A
I_{FRM}	$I_{FRM} = 1,33 \times I_{Fnom}$			800	A
Module					
$I_{t(RMS)}$				500	A
T_{vj}				- 40 + 175	$^\circ\text{C}$
T_{stg}				- 40 + 125	$^\circ\text{C}$
V_{isol}	AC, 1 min.			4000	V

Characteristics			T _{case} = 25°C, unless otherwise specified			
Symbol	Conditions		min.	typ.	max.	Units
IGBT						
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 9,6 mA		5	5,8	6,5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = V _{CES}	T _j = 25 °C		0,3	0,9	mA
V _{CE0}		T _j = 25 °C		0,9	1	V
		T _j = 150 °C		0,85	0,9	V
r _{CE}	V _{GE} = 15 V	T _j = 25°C		0,9	1,5	mΩ
		T _j = 150°C		1,4	2	mΩ
V _{CE(sat)}	I _{Cnom} = 600 A, V _{GE} = 15 V	T _j = 25°C _{chiplev.}		1,45	1,9	V
		T _j = 150°C _{chiplev.}		1,7	2,1	V
C _{ies}	V _{CE} = 25, V _{GE} = 0 V	f = 1 MHz		37		nF
C _{oes}				2,3		nF
C _{res}				1,1		nF
Q _G	V _{GE} = -8V...+15V			4400		nC
R _{Gint}	T _j = °C			0,5		Ω
t _{d(on)}	R _{Gon} = 1,5 Ω	V _{CC} = 300V I _C = 600A T _j = 150 °C V _{GE} = -8V/+15V		270		ns
t _r				77		ns
E _{on}			7,5		mJ	
t _{d(off)}	R _{Goff} = 1,5 Ω			670		ns
t _f				77		ns
E _{off}			29,5		mJ	
R _{th(j-c)}	per IGBT				0,08	K/W

SKM 600GB066D



SEMITRANS® 3

Trench IGBT Modules

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Features

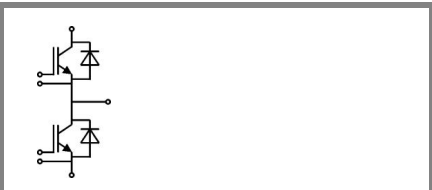
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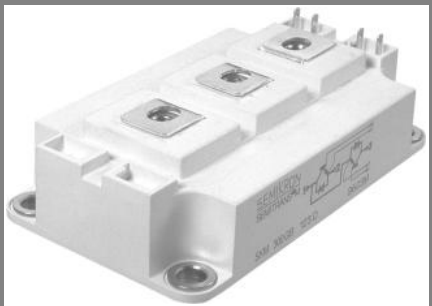
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Units
Inverse Diode						
V _F = V _{EC}	I _{Fnom} = 600 A; V _{GE} = 0 V	T _j = 25 °C _{chiplev.}		1,4	1,6	V
V _{F0}		T _j = 25 °C		0,95	1	V
r _F		T _j = 25 °C		0,8	1	mΩ
I _{RRM}	I _F = 600 A	T _j = 150 °C		580		A
Q _{rr}	di/dt = 8600 A/μs			105		μC
E _{rr}	V _{GE} = -8 V; V _{CC} = 300 V			25		mJ
R _{th(j-c)D}	per diode				0,125	K/W
Module						
L _{CE}				15	20	nH
R _{CC'+EE'}	res., terminal-chip	T _{case} = 25 °C		0,35		mΩ
		T _{case} = 125 °C		0,5		mΩ
R _{th(c-s)}	per module				0,038	K/W
M _s	to heat sink M6		3		5	Nm
M _t	to terminals M6		2,5		5	Nm
w					325	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

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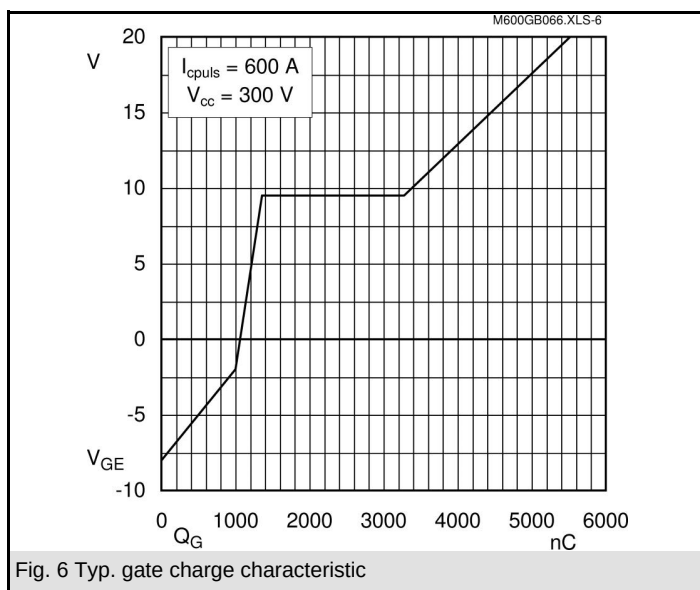
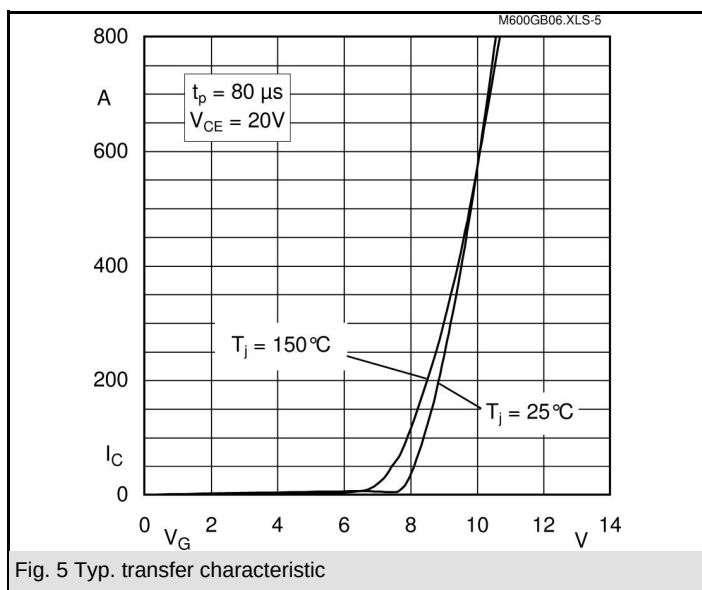
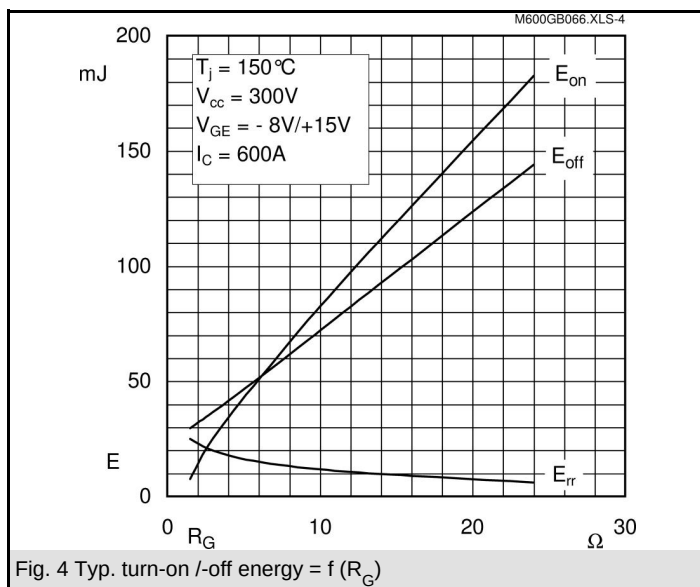
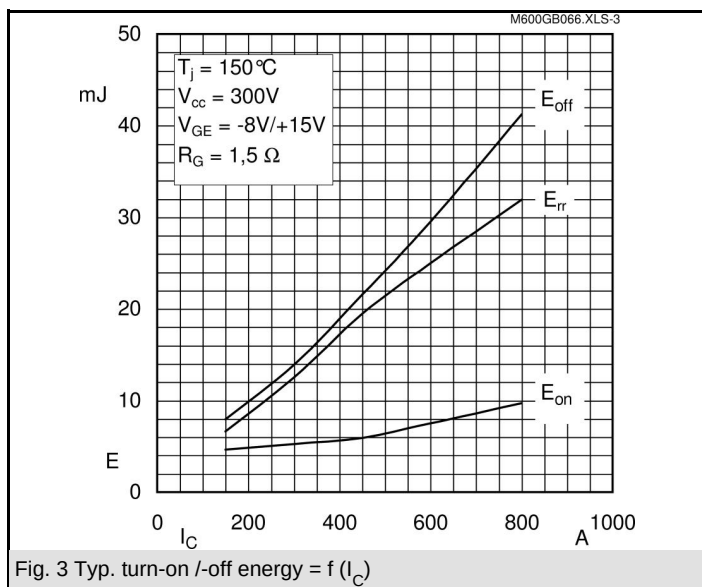
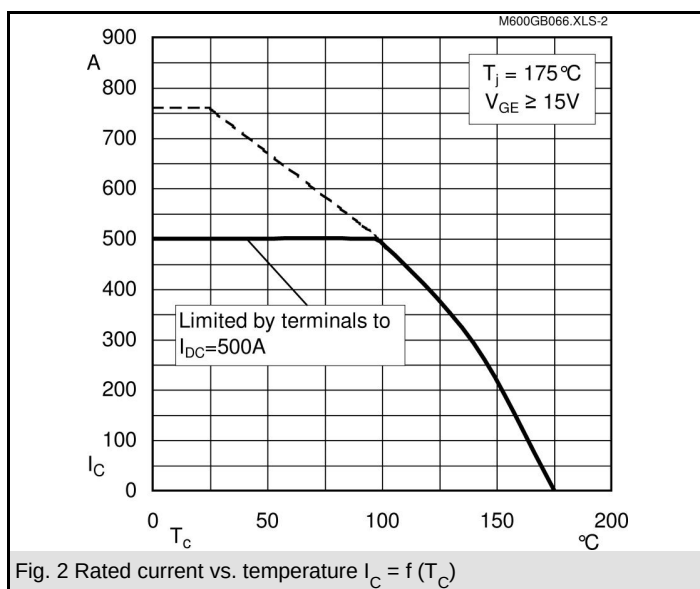
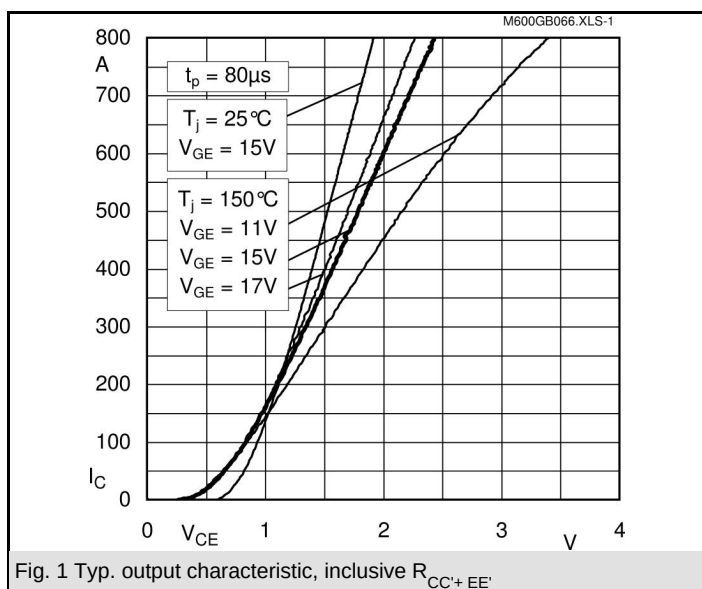
Remarks

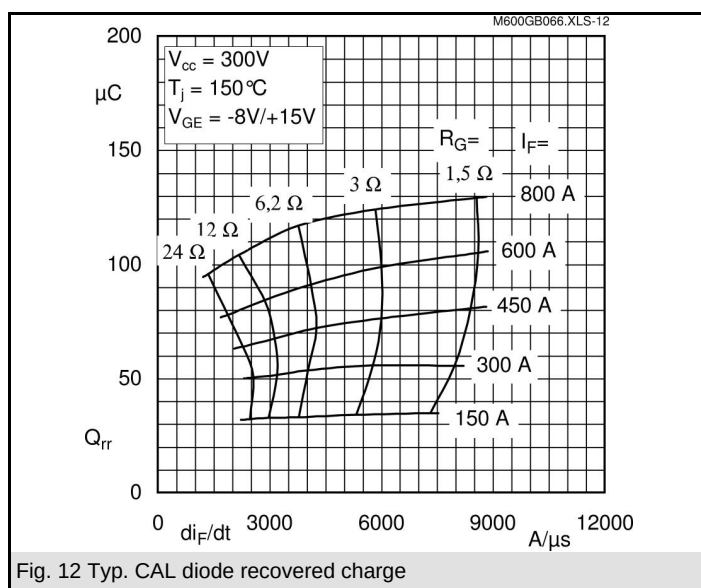
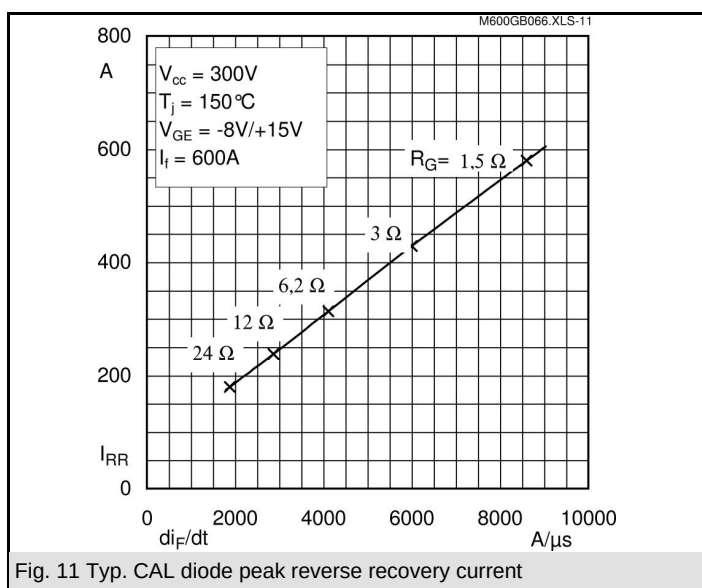
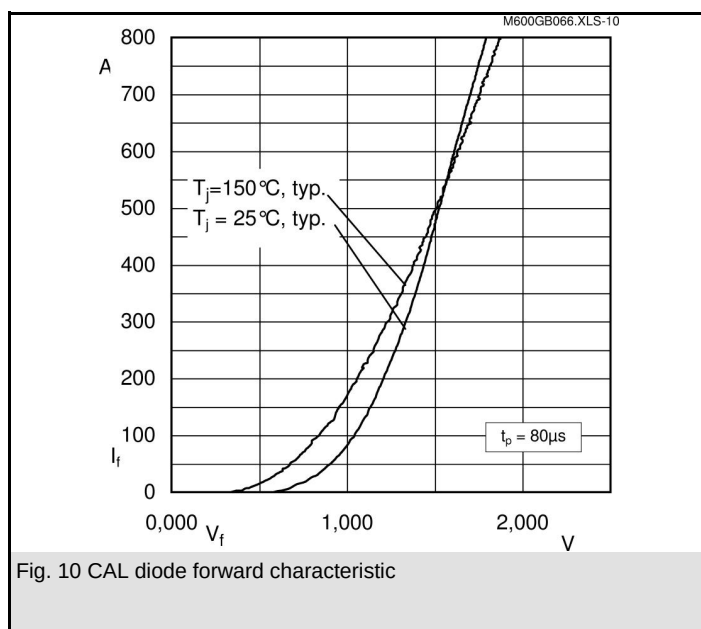
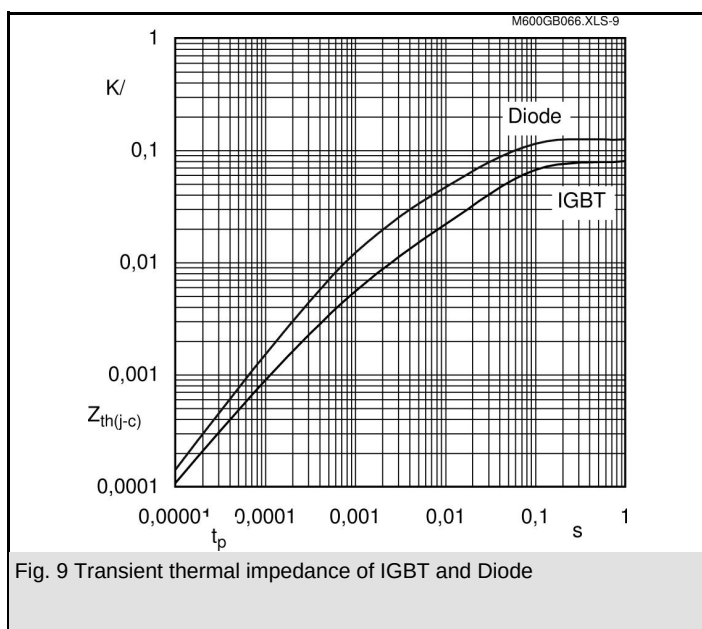
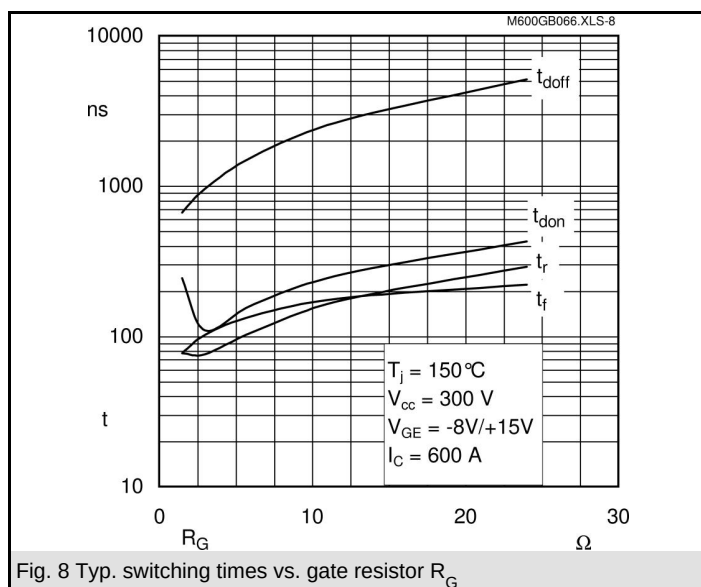
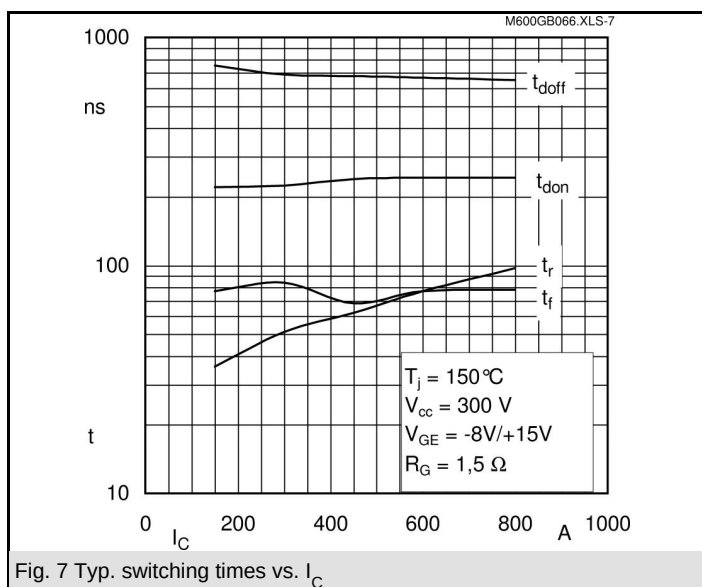
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Z_{th}			
Symbol	Conditions	Values	Units
$Z_{th(j-c)I}$			
R_i	$i = 1$	48,4	mk/W
R_i	$i = 2$	19,5	mk/W
R_i	$i = 3$	3,1	mk/W
R_i	$i = 4$	4	mk/W
τ_{u_i}	$i = 1$	0,054	s
τ_{u_i}	$i = 2$	0,0144	s
τ_{u_i}	$i = 3$	0,0012	s
τ_{u_i}	$i = 4$	0,0026	s
$Z_{th(j-c)D}$			
R_i	$i = 1$	80	mk/W
R_i	$i = 2$	33	mk/W
R_i	$i = 3$	10,5	mk/W
R_i	$i = 4$	1,5	mk/W
τ_{u_i}	$i = 1$	0,054	s
τ_{u_i}	$i = 2$	0,01	s
τ_{u_i}	$i = 3$	0,0007	s
τ_{u_i}	$i = 4$	0,0019	s



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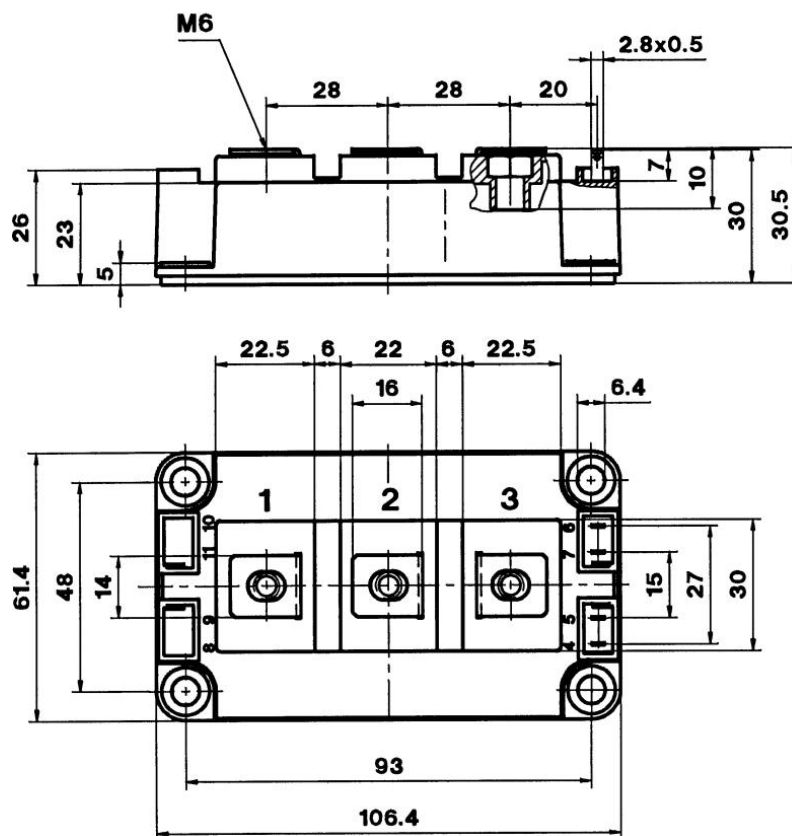




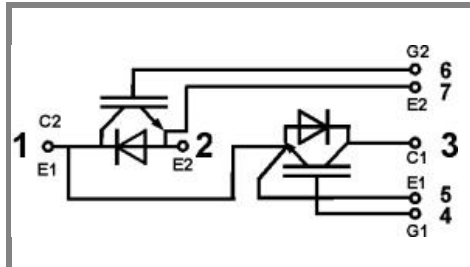
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